

**SANYO**

No.5267

**2SJ417**

P-Channel Silicon MOSFET

Ultrahigh-Speed Switching Applications

**Features**

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

**Absolute Maximum Ratings at Ta = 25°C**

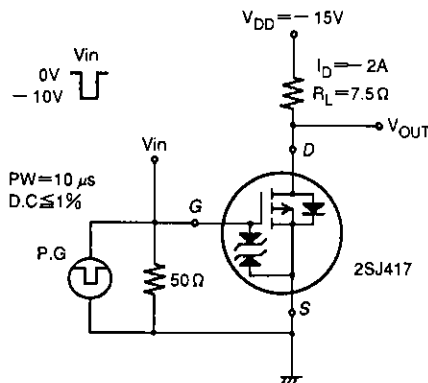
			unit
Drain-to-Source Voltage	V <sub>DSS</sub>	-30	V
Gate-to-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current(DC)	I <sub>D</sub>	-4	A
Drain Current(Pulse)	I <sub>DP</sub>	-16	A
Allowable Power Dissipation	P <sub>D</sub>	1	W
		Tc = 25°C	
Channel Temperature	Tch	20	W
Storage Temperature	Tstg	150	°C
		-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

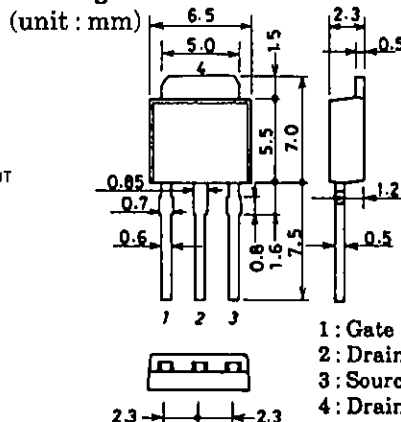
			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1mA, V <sub>GS</sub> = 0	-30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0			-100	µA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0			±10	µA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA	-1.0		-2.5	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -2A	2	4		S
Static Drain-to-Source ON-State Resistance	R <sub>DSON</sub>	I <sub>D</sub> = -2A, V <sub>GS</sub> = -10V		120	160	mΩ
ON-State Resistance	R <sub>DSON</sub>	I <sub>D</sub> = -2A, V <sub>GS</sub> = -4V		210	290	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		370		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		230		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		70		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		10		ns
Rise Time	t <sub>r</sub>	"		50		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	"		135		ns
Fall Time	t <sub>f</sub>	"		125		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -4A, V <sub>GS</sub> = 0	-1.0	-1.2		V

Marking : JJ

**Switching Time Test Circuit**

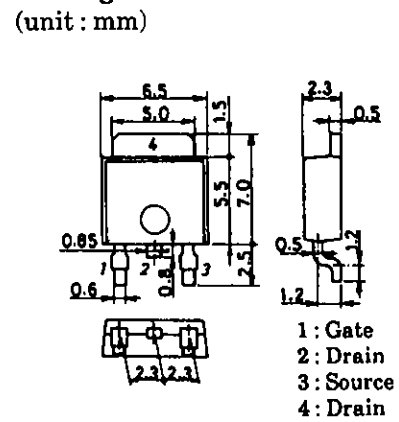


**Package Dimensions 2083B**



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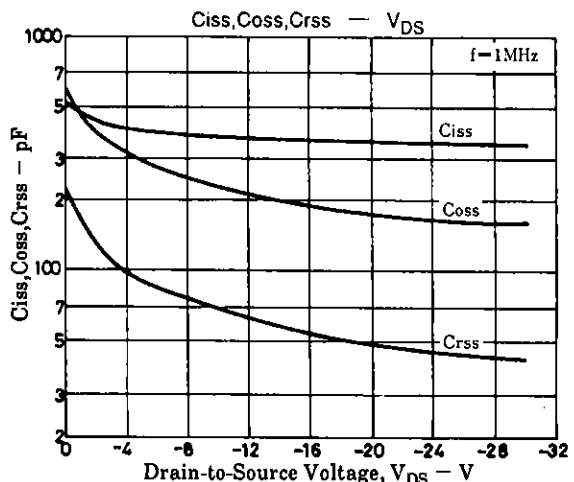
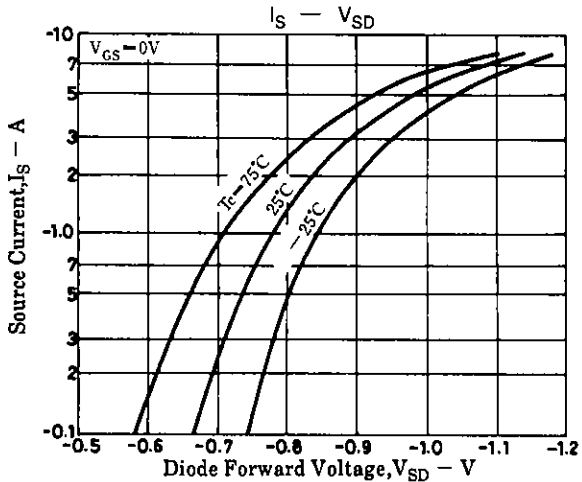
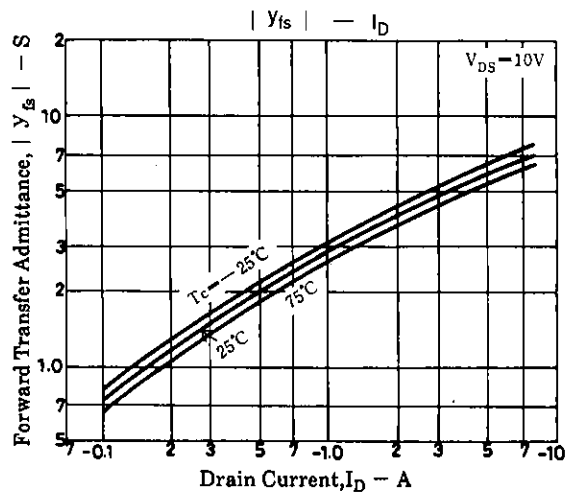
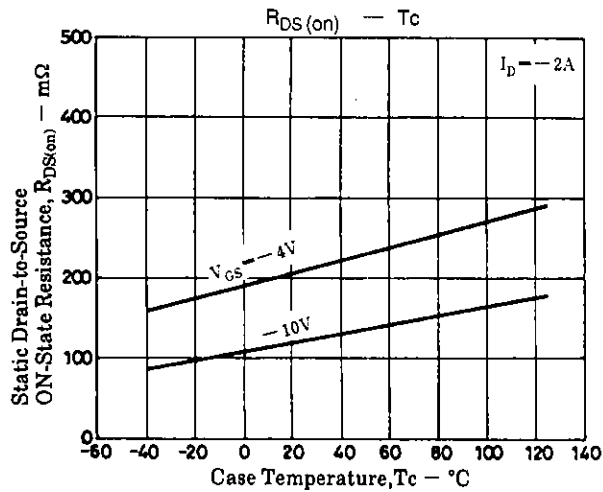
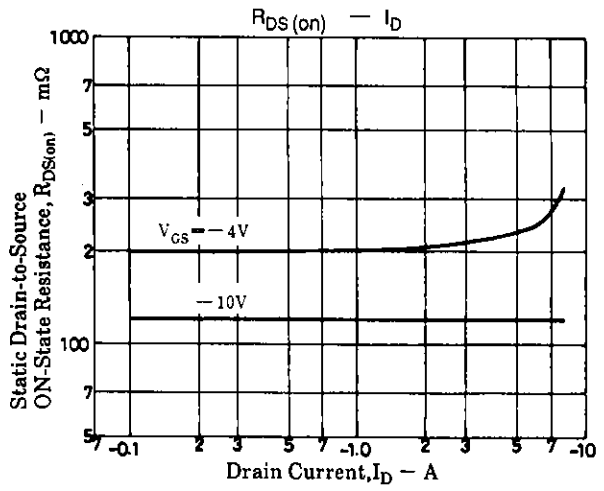
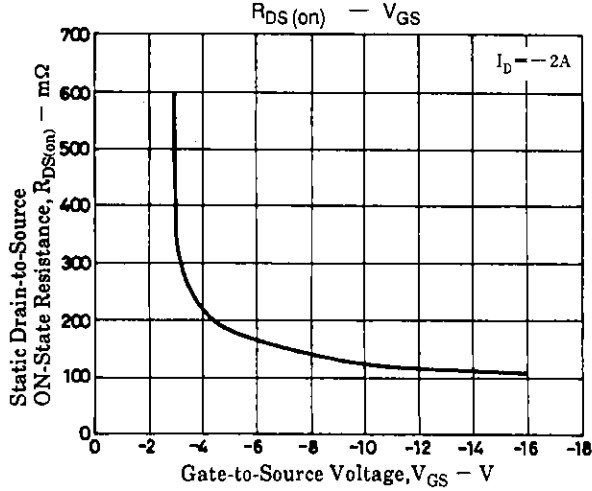
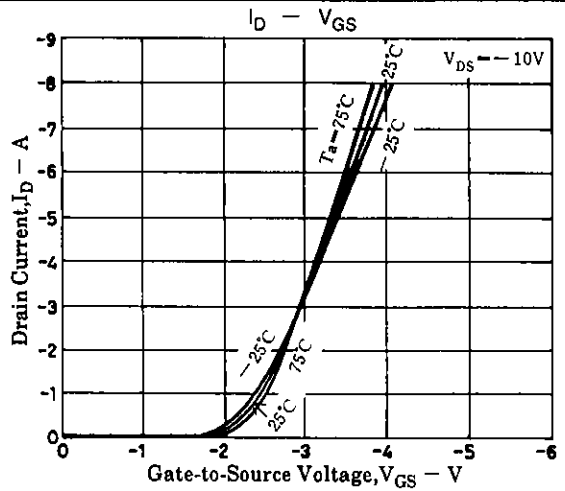
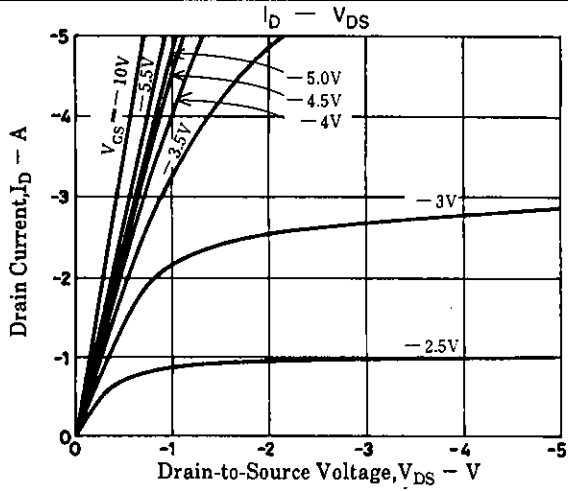
**Package Dimensions 2092B**

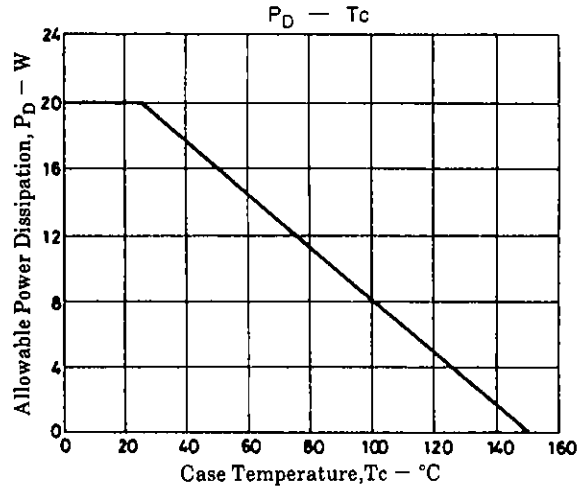
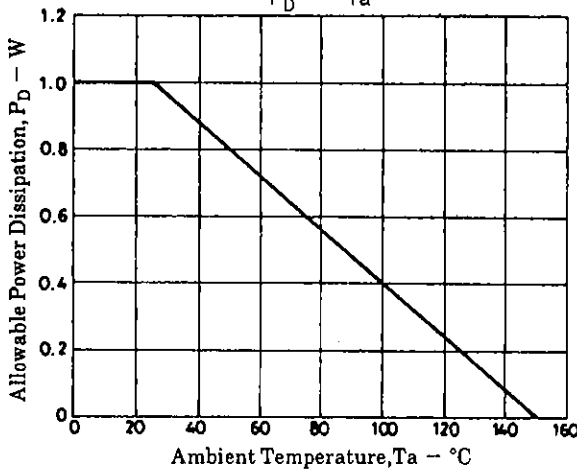
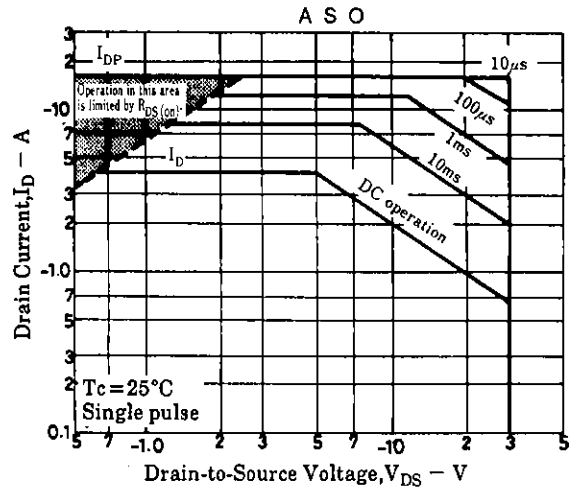
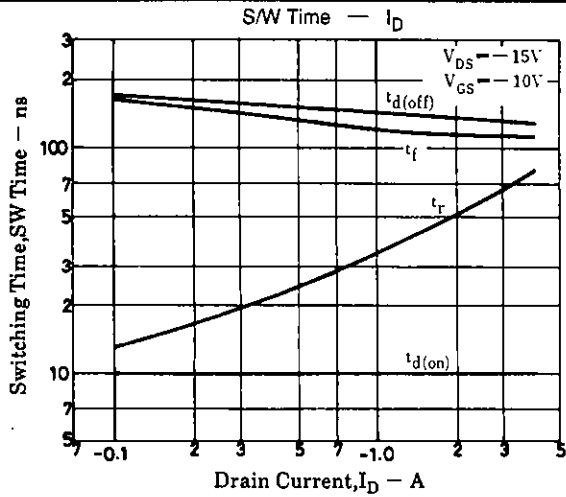


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